

Silicon PNP Power Transistors

2SA1106

DESCRIPTION

- With TO-3PN package
- High frequency
- High power dissipation

APPLICATIONS

- Audio power amplifier applications
- DC-DC converters

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

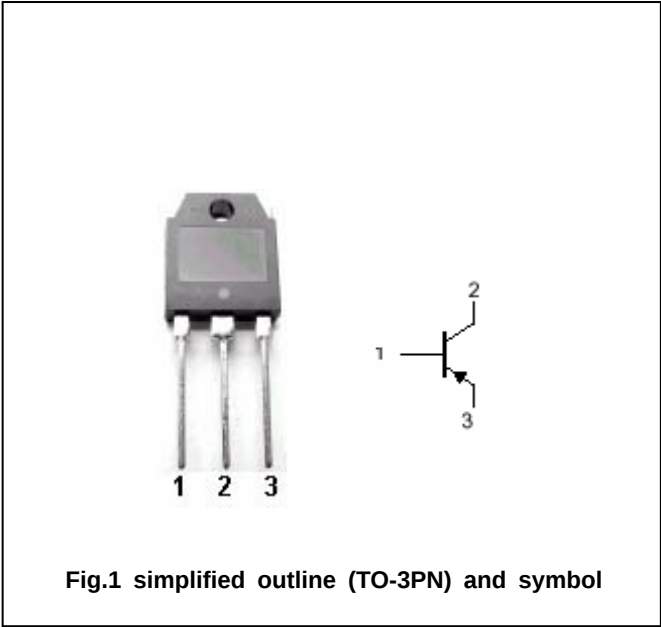


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-200	V
V _{CEO}	Collector-emitter voltage	Open base	-140	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-10	A
P _C	Collector power dissipation	T _C =25	100	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-25mA$; $I_B=0$	-140			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-5A$; $I_B=-0.5A$			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-5A$; $I_B=-0.5A$			-1.8	V
I_{CBO}	Collector cut-off current	$V_{CB}=-140V$; $I_E=0$			-100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-6V$; $I_C=0$			-100	μA
h_{FE}	DC current gain	$I_C=-5A$; $V_{CE}=4V$	50		180	
f_T	Transition frequency	$I_E=1A$; $V_{CE}=-12V$		20		MHz

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PACKAGE OUTLINE

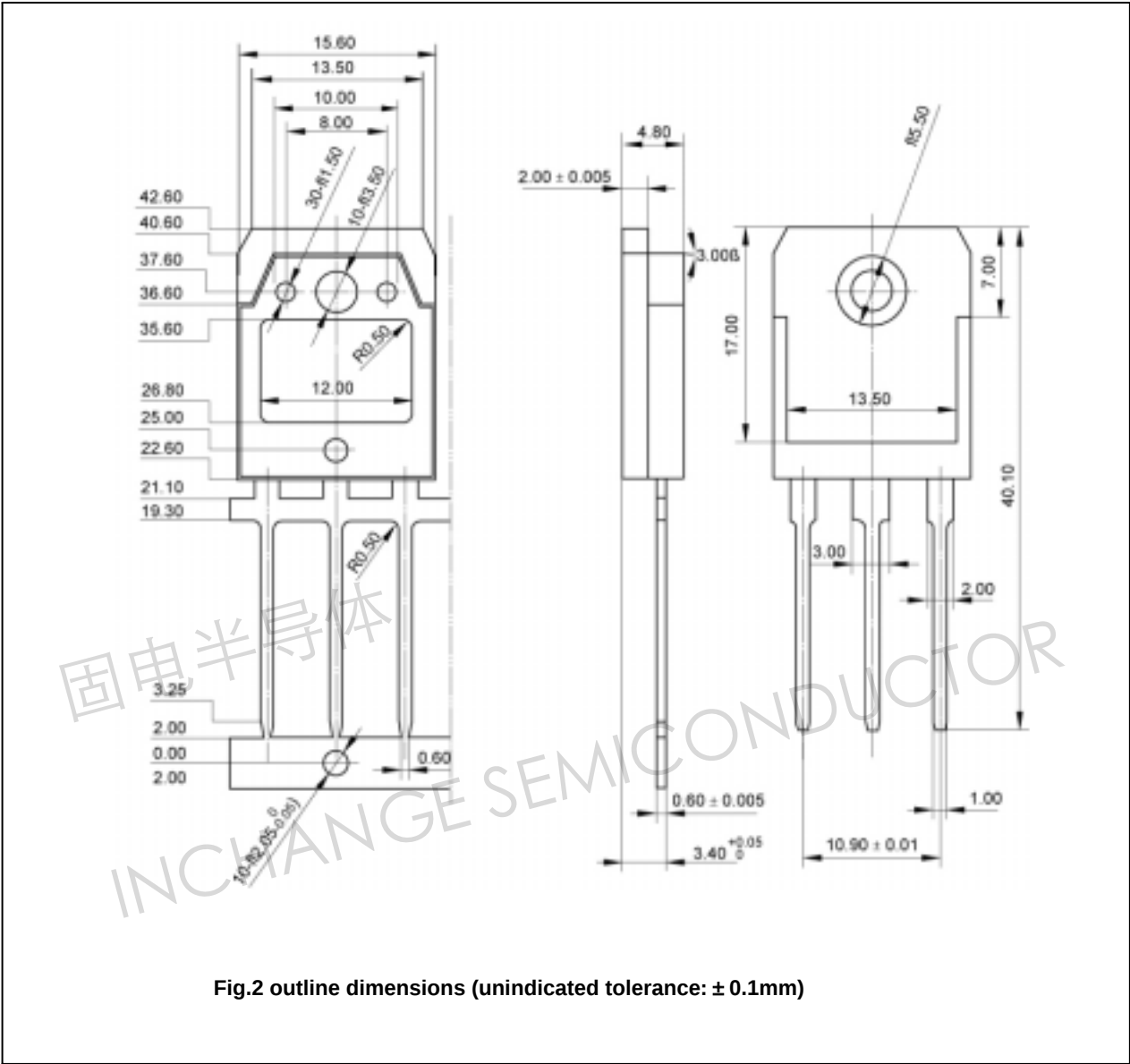


Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)